

Notice of References Cited	Application/Control No.	Applicant(s)/Patent Under Reexamination SAMOLOV ET AL.	
	Examiner Robert M Kunemund	Art Unit 1765	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-5,714,777	02-1998	Ismail et al	257/263
	C	US-3,985,590	10-1976	Mason	-----
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	U	Liu et al., "A surfactant-mediated relaxed Si Ge graded layer with a very low threading dislocation density and smooth surface", Applied Physics Letters vol 75 no. 11 pages 1586-1588 Sept 13, 1999.
	V	Pogossian et al., "Analysis of high confinement SiGe/Si waveguides for silicon based optoelectronics", J. Opt Soc. Am A vol 16, no. 3 March 1999 pages 591-595
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.